

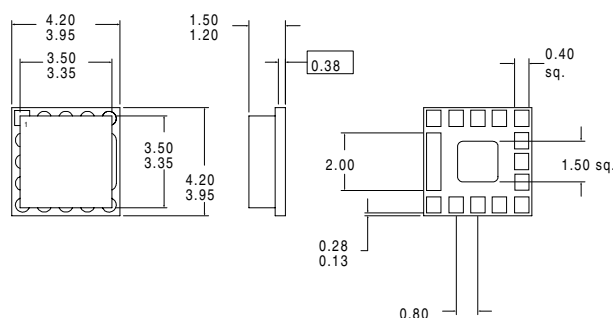
### 3V WCDMA POWER 1900MHZ 3V LINEAR POWER AMPLIFIER

#### Typical Applications

- 3V 1850-1910 CDMA-2000 Handsets
- 3V 1920-1980 WCDMA Handsets
- Spread Spectrum Systems
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment

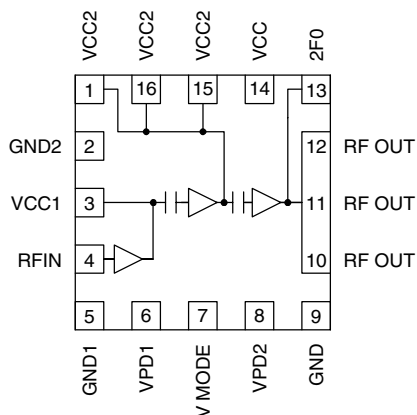
#### Product Description

The RF2161 is a high-power, high-efficiency linear amplifier IC targeting 3V handheld systems. The device is manufactured on an advanced Gallium Arsenide Hetero-junction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 3V CDMA-2000 and WCDMA handsets, spread spectrum systems, and other applications in the 1920MHz to 1980 MHz band. The device is self-contained with 50Ω input and the output can be easily matched to obtain optimum power, efficiency, and linearity characteristics over all recommended supply voltages.



#### Optimum Technology Matching® Applied

- |                                     |  |                                      |
|-------------------------------------|--|--------------------------------------|
| <input type="checkbox"/> Si BJT     | <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> GaAs MESFET |
| <input type="checkbox"/> Si Bi-CMOS | <input type="checkbox"/> SiGe HBT            | <input type="checkbox"/> Si CMOS     |



Functional Block Diagram

#### Package Style: MP16KO1A

#### Features

- Single 3V Supply
- 27dBm Linear Output Power
- 30dB Linear Gain
- 35% Linear Efficiency
- On-board Power Down Mode

#### Ordering Information

RF2161	3V WCDMA Power 1900MHZ 3V Linear Power Amplifier
RF2161 PCBA	Fully Assembled Evaluation Board

RF Micro Devices, Inc.  
7625 Thorndike Road  
Greensboro, NC 27409, USA

Tel (336) 664 1233  
Fax (336) 664 0454  
<http://www.rfmd.com>

## Absolute Maximum Ratings

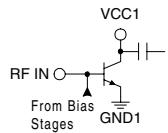
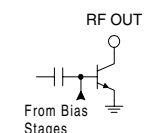
Parameter	Rating	Unit
Supply Voltage (RF off)	+8.0	V <sub>DC</sub>
Supply Voltage (P <sub>OUT</sub> ≤ 31 dBm)	+5.0	V <sub>DC</sub>
Mode Voltage (V <sub>MODE</sub> )	+3.0	V <sub>DC</sub>
Control Voltage (V <sub>PD</sub> )	+3.0	V <sub>DC</sub>
Input RF Power	+6	dBm
Operating Case Temperature	-30 to +100	°C
Storage Temperature	-30 to +150	°C



Caution! ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					T = 25 °C, V <sub>CC</sub> = 3.4 V unless otherwise specified
Usable Frequency Range	1850		2000	MHz	
Typical Frequency Range		1850 to 1910 1920 to 1980		MHz	
Linear Gain	28	30		dB	Mode = Low
	26	28		dB	Mode = High
Second Harmonic (including second harmonic trap)		-35		dBc	
Third Harmonic		-40		dBc	
Fourth Harmonic		-45		dBc	
Maximum Linear Output Power (WCDMA Modulation)	27			dBm	
Total Linear Efficiency	30	35		%	
Adjacent Channel Power Rejection @ 5 MHz	-45	-40	-38	dBc	P <sub>OUT</sub> = 27 dBm, WCDMA Modulation
Adjacent Channel Power Rejection @ 10 MHz	-60	-50	-48	dBc	P <sub>OUT</sub> = 27 dBm, WCDMA Modulation
Noise Power		-92		dBc	P <sub>OUT</sub> = +27 dBm, 30 kHz BW Rx Band 2110 MHz to 2170 MHz
Maximum Linear Output Power (WCDMA Modulation)	27			dBm	V <sub>CC</sub> = 3.0 V
Total Linear Efficiency		36		%	
Input VSWR		< 2:1			
Output Load VSWR			5:1		No oscillations
<b>Power Supply</b>					
Power Supply Voltage	3.0	3.4	5.0	V	
Idle Current		120		mA	MODE = high
V <sub>PD</sub> Current		10		mA	Total pins 7 and 8, V <sub>PD</sub> = 2.8 V
Turn On/Off time			100	ns	
Total Current (Power down)			10	μA	V <sub>PD</sub> = low
V <sub>PD</sub> "Low" Voltage		0	0.2	V	
V <sub>PD</sub> "High" Voltage	2.7	2.8	2.9	V	
MODE "High" Voltage	2.5	2.8			
MODE "Low" Voltage		0	0.5		

Pin	Function	Description	Interface Schematic
1	VCC2	Power supply for second stage and interstage match. Pins 1, 15 and 16 should be connected by a common trace where the pins contact the printed circuit board.	
2	GND2	Ground for second stage. For best performance, keep traces physically short and connect immediately to ground plane. This ground should be isolated from the backside ground contact.	
3	VCC1	Power supply for first stage and interstage match. V <sub>CC</sub> should be fed through a 1.2nH inductor terminated with a 8.2pF capacitor on the supply side. The inductor should be as close to the pin as possible.	See pin 4.
4	RF IN	RF input. An external series capacitor is required as a DC block. The input match can be improved to <2:1 by using a series capacitor and shunt inductor.	
5	GND1	Ground for first stage. For best performance, keep traces physically short and connect immediately to ground plane. This ground should be isolated from the backside ground contact.	See pin 4.
6	VPD1	Power Down control for first and second stages. When this pin is "low", all first and second stage circuits are shut off. When this pin is 2.8V, all first and second stage circuits operate normally. V <sub>PD1</sub> requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V.	
7	VMODE	V <sub>MODE</sub> adjusts the bias to the 2nd and 3rd stages. For full power operation, MODE is set low. When operating in a lower output power mode (<+25dBm) this pin is set high to reduce bias current by up to 50%. An external series resistor is optional to limit the amount of current required. At low temperature (-30°C), it is recommended to set V <sub>MODE</sub> low to maintain correct operation.	
8	VPD2	Power Down control for third stage. When this pin is "low", all and third stage circuits are shut off. When this pin is 2.8V, all and third stage circuits operate normally. V <sub>PD</sub> requires a regulated 2.8V for the amplifier to operate properly over all specified temperature and voltage ranges. A dropping resistor from a higher regulated voltage may be used to provide the required 2.8V. A 12pF high frequency bypass capacitor is recommended.	
9	GND	For best performance, keep traces physically short and connect immediately to ground plane. This ground should be isolated from the backside ground contact.	
10	RF OUT	RF output and power supply for final stage. This is the unmatched collector output of the third stage. A DC block is required following the matching components. The biasing may be provided via a parallel L-C set for resonance at the operating frequency of 1920MHz to 1980MHz. It is important to select an inductor with very low DC resistance with a 1A current rating. Alternatively, shunt microstrip techniques are also applicable and provide very low DC resistance. Low frequency bypassing is required for stability.	
11	RF OUT	Same as pin 10.	See pin 10.
12	RF OUT	Same as pin 10.	See pin 10.
13	2FO	Second harmonic trap. Keep traces physically short and connect immediately to ground plane. This ground should be isolated from backside ground contact.	
14	VCC	Supply for bias reference and control circuits. High frequency bypassing may be necessary.	
15	VCC2	Same as Pin 1.	
16	VCC2	Same as Pin 1.	

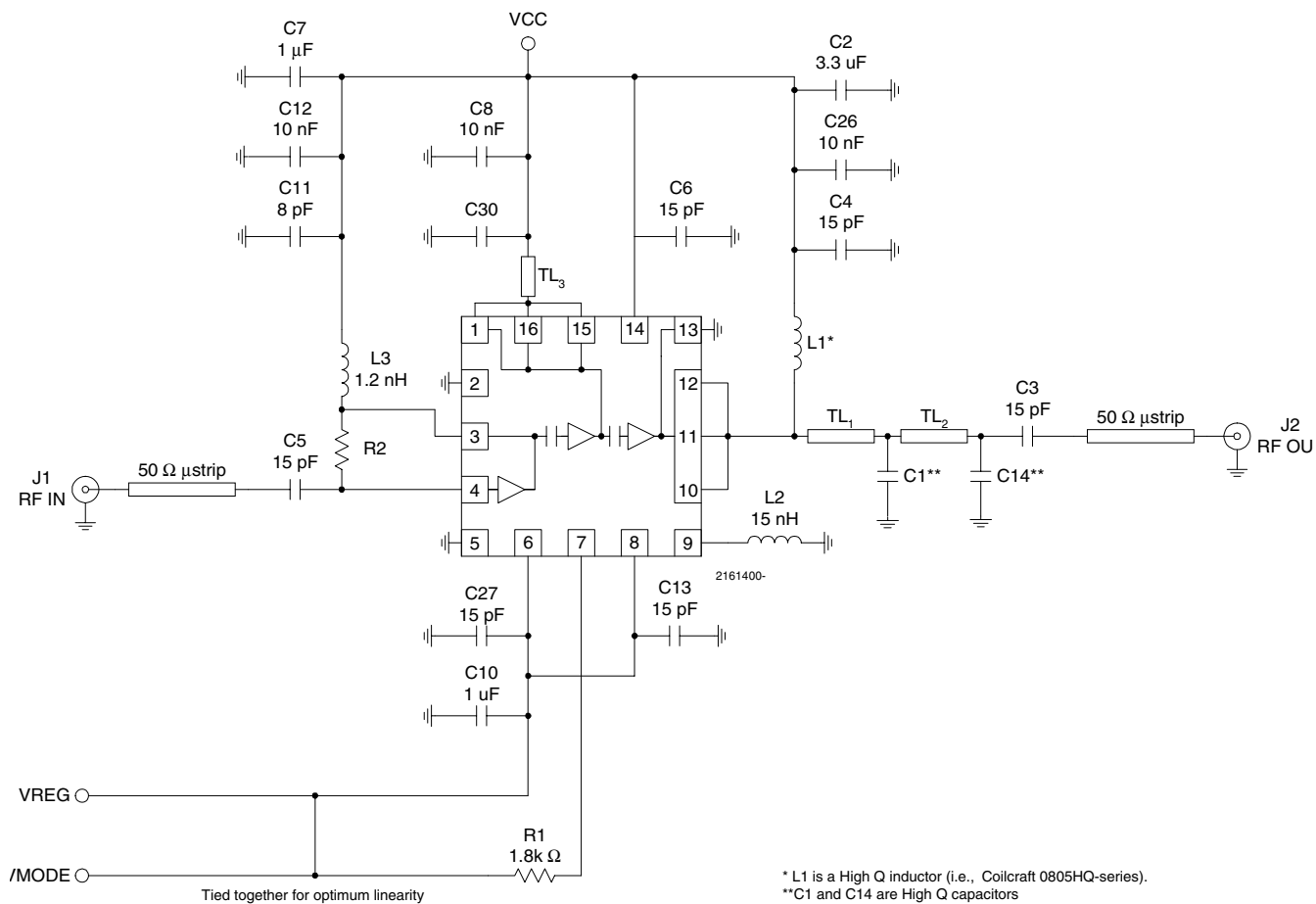
Pin	Function	Description	Interface Schematic
<b>Pkg Base</b>	<b>GND</b>	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

Transmission Line Length	$TL_1$	$TL_2$	$TL_3$
WCDMA	0.067"	0.130"	0.022"

## Evaluation Board Schematic WCDMA (1920MHz to 1980MHz)

2

POWER AMPLIFIERS



Board	R2 ( $\Omega$ )	C30 (pF)	C1 (pF)	L1 (nH)	C14 (pF)
WCDMA	150	10	4.7	16	2.2

Transmission Line Length	TL <sub>1</sub>	TL <sub>2</sub>	TL <sub>3</sub>
WCDMA	0.067"	0.130"	0.022"

## Evaluation Board Layout Board Size 2.00" x 2.00"

Board Thickness 0.28", Board Material FR-4, Multi-Layer

